

FEATURES :

- HIGH POWER
 $P_{1dB} = 47.0 \text{ dBm}$ at 1.9 GHz
- HIGH GAIN
 $G_{1dB} = 13 \text{ dB}$ at 1.9 GHz
- PARTIALLY MATCHED TYPE
- HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS ($T_a = 25^\circ\text{C}$)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Compression Point	P_{1dB}	$V_{DS} = 10 \text{ V}$ $f = 1.9 \text{ GHz}$	dBm	46.0	47.0	—
Power Gain at 1dB Compression Point	G_{1dB}		dB	12.0	13.0	—
Drain Current	I_{DS}		A	—	9.6	11.0
Power Added Efficiency	η_{add}		%	—	49	—
Channel-Temperature Rise	ΔT_{ch}	$V_{DS} \times I_{DS} \times R_{th(c-c)}$	$^\circ\text{C}$	—	—	100

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	$V_{DS} = 3 \text{ V}$ $I_{DS} = 11.0 \text{ A}$	mS	—	8800	—
Pinch-off Voltage	V_{GSoff}	$V_{DS} = 3 \text{ V}$ $I_{DS} = 170 \text{ mA}$	V	-1.0	-2.5	-4.0
Saturated Drain Current	I_{DSS}	$V_{DS} = 3 \text{ V}$ $V_{GS} = 0 \text{ V}$	A	—	24	31
Gate-Source Breakdown Voltage	V_{GSO}	$I_{GS} = -500 \mu\text{A}$	V	-5	—	—
Thermal Resistance	$R_{th(c-c)}$	Channel to Case	$^\circ\text{C/W}$	—	0.8	1.2

* RECOMMENDED GATE RESISTANCE (R_g) : $R_g = 30 \Omega$ (MAX.)

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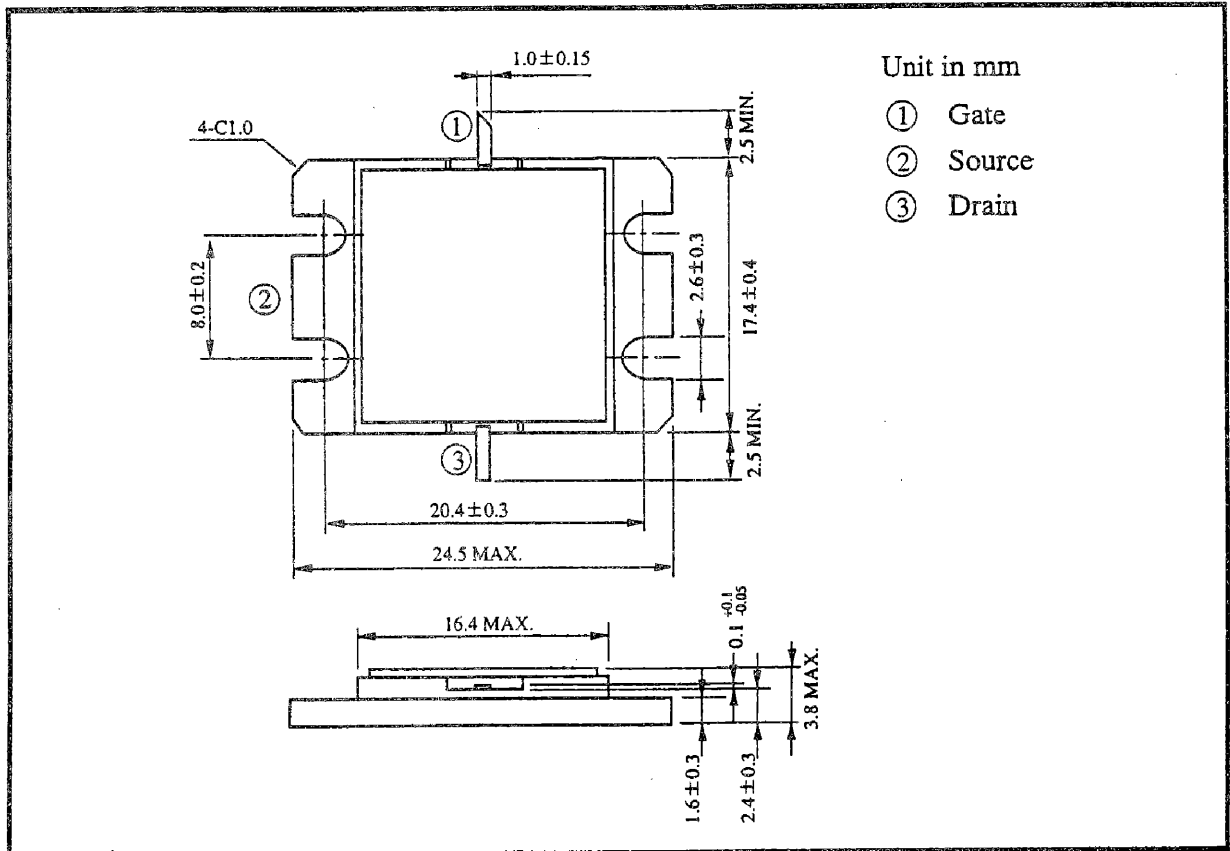


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ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	31
Total Power Dissipation (T _C = 25°C)	P _T	W	125
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65~175

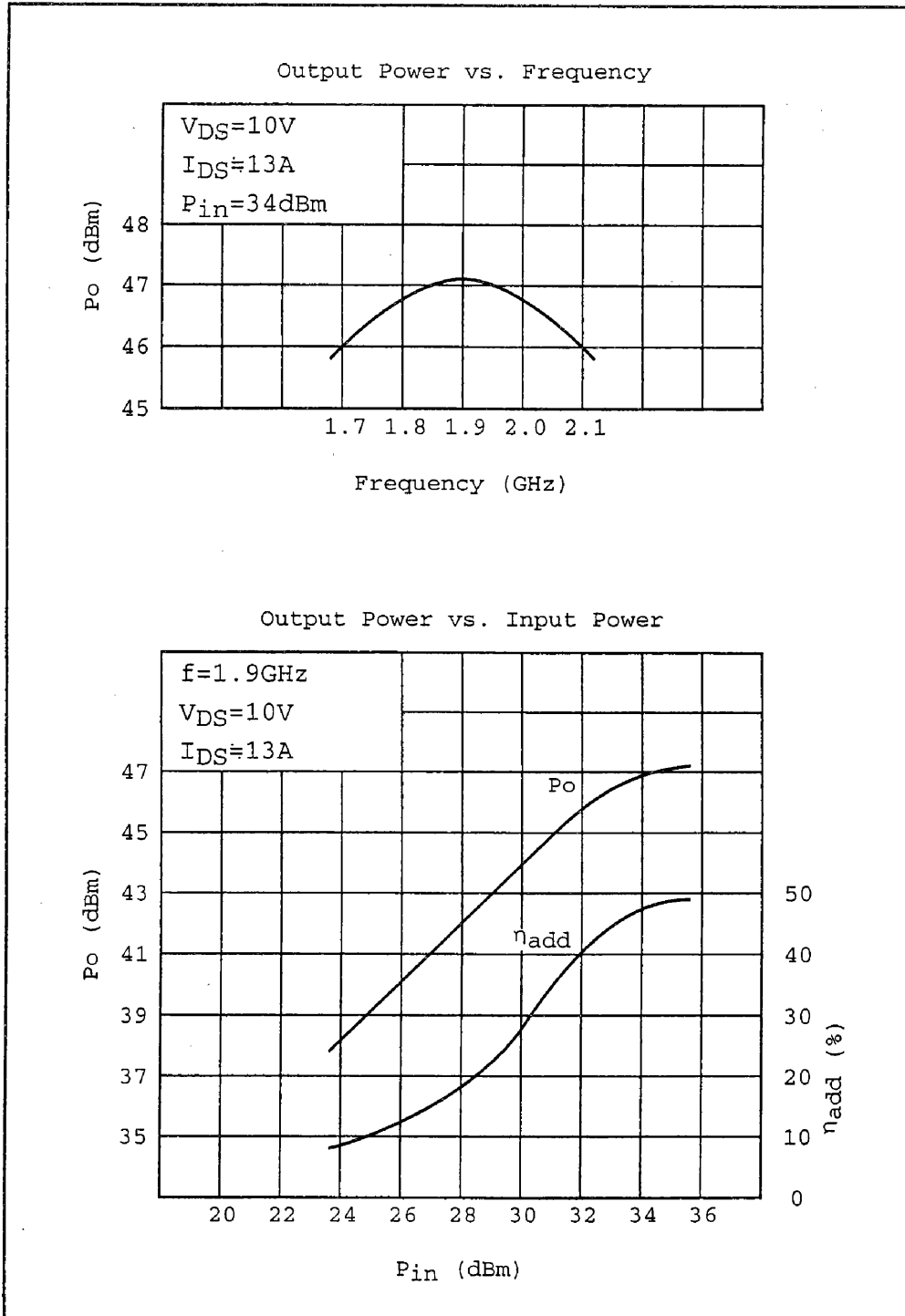
PACKAGE OUTLINE (2-16G6A)



HANDLING PRECAUTIONS FOR PACKAGED TYPE

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF PERFORMANCES.



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POWER DISSIPATION VS. CASE TEMPERATURE

